

SSP7411P-VB Datasheet

P-Channel 100-V (D-S) MOSFET

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
- 100	0.032 at $V_{GS} = - 10$ V	- 28	7.6 nC
	0.036 at $V_{GS} = - 4.5$ V	- 25	

FEATURES

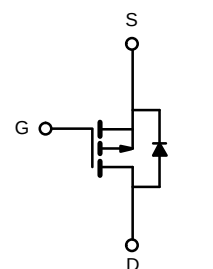
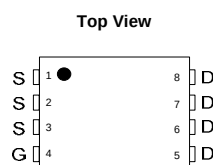
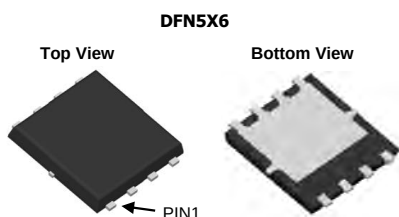
- Trench Power MOSFET
- 100 % UIS Tested

APPLICATIONS

- Load Switch



RoHS
COMPLIANT
HALOGEN
FREE



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	- 100	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	A
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Pulsed Drain Current	I_{DM}	- 15	mJ
Avalanche Current Pulse	I_{AS}	- 4.5	
Single Pulse Avalanche Energy	E_{AS}	10.1	
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	A
		$T_A = 25$ °C	
Maximum Power Dissipation	P_D	$T_C = 25$ °C	W
		$T_C = 70$ °C	
		$T_A = 25$ °C	
		$T_A = 70$ °C	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^b	R_{thJA}	33	40	°C/W
Maximum Junction-to-Case	R_{thJC}	0.98	1.2	

Notes:

a. Based on $T_C = 25$ °C.

b. Surface mounted on 1" x 1" FR4 board.

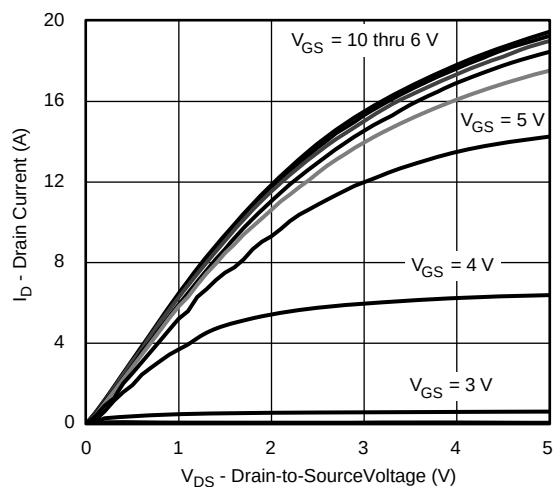
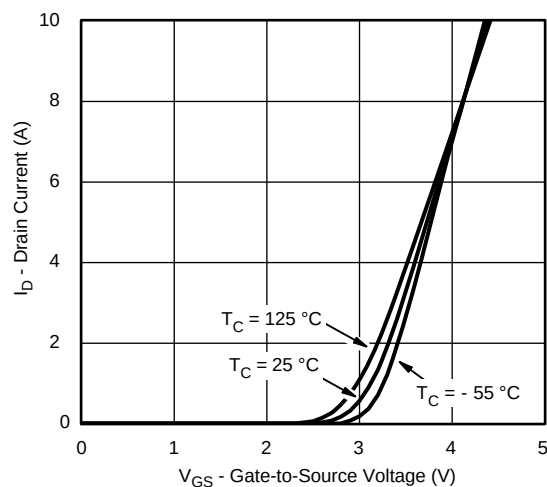
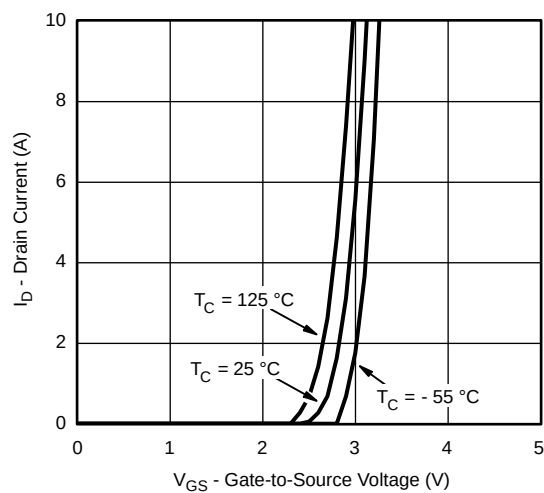
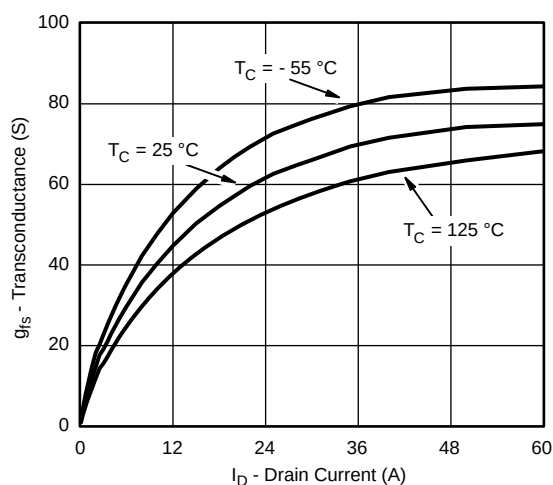
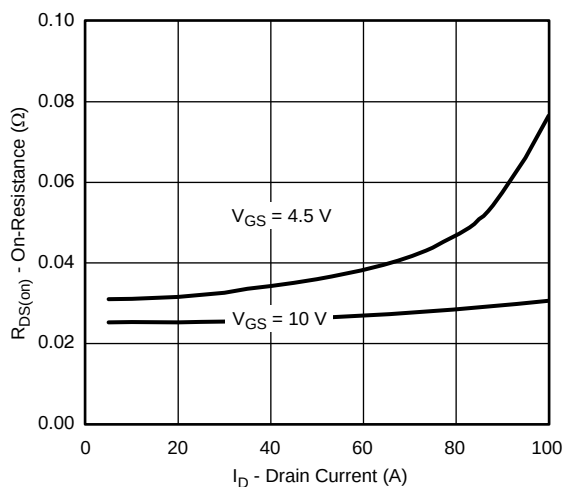
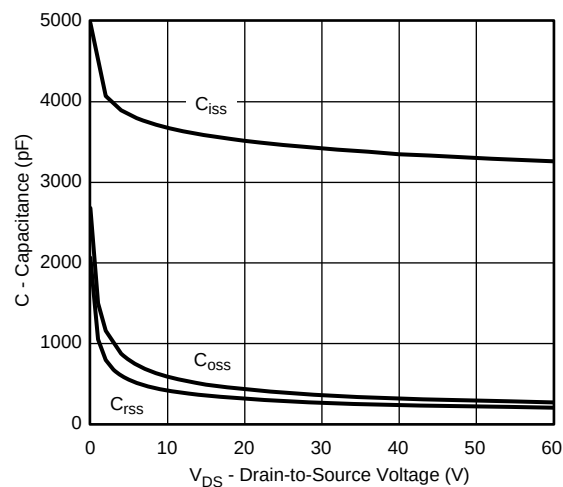
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)							
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = - 250 μA	- 100			V	
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	I _D = - 250 μA		68		mV/°C	
V _{GS(th)} Temperature Coefficient	ΔV _{GS(th)} /T _J			- 5.2			
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = - 250 μA	- 1.8		- 3	V	
Gate-Source Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ± 20 V			± 100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 100 V, V _{GS} = 0 V			- 1	μA	
		V _{DS} = - 100 V, V _{GS} = 0 V, T _J = 55 °C			- 10		
On-State Drain Current ^a	I _{D(on)}	V _{DS} = - 5 V, V _{GS} = - 10 V	- 120			A	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 3 A		0.032		Ω	
		V _{GS} = - 4.5 V, I _D = - 2 A		0.036			
Forward Transconductance ^a	g _{fs}	V _{DS} = - 15 V, I _D = - 5 A	20			S	
Dynamic ^b							
Input Capacitance	C _{iss}	V _{DS} = - 25 V, V _{GS} = 0 V, f = 1 MHz		3500		pF	
Output Capacitance	C _{oss}			390			
Reverse Transfer Capacitance	C _{rss}			290			
Total Gate Charge	Q _g	V _{DS} = - 30 V, V _{GS} = - 10 V, I _D = - 5 A		76	115	nC	
Gate-Source Charge	Q _{gs}	V _{DS} = - 30 V, V _{GS} = - 4.5 V, I _D = - 5 A		38	60		
Gate-Drain Charge	Q _{gd}			16			
Gate Resistance	R _g			19			
Turn-On Delay Time	t _{d(on)}	f = 1 MHz		5.2		Ω	
Rise Time	t _r		V _{DD} = - 2 V, R _L = 2 Ω I _D ≅ - 5 A, V _{GEN} = - 10 V, R _g = 1 Ω		10	15	ns
Turn-Off Delay Time	t _{d(off)}				7	15	
Fall Time	t _f				70	110	
				40	60		
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			- 6.9	A	
Pulse Diode Forward Current ^a	I _{SM}				- 15		
Body Diode Voltage	V _{SD}	I _S = - 3 A		- 1	- 1.5	V	
Body Diode Reverse Recovery Time	t _{rr}	I _F = - 5 A, di/dt = 10 A/μs, T _J = 25 °C		45	68	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			59	120	nC	
Reverse Recovery Fall Time	t _a			29		ns	
Reverse Recovery Rise Time	t _b			16			

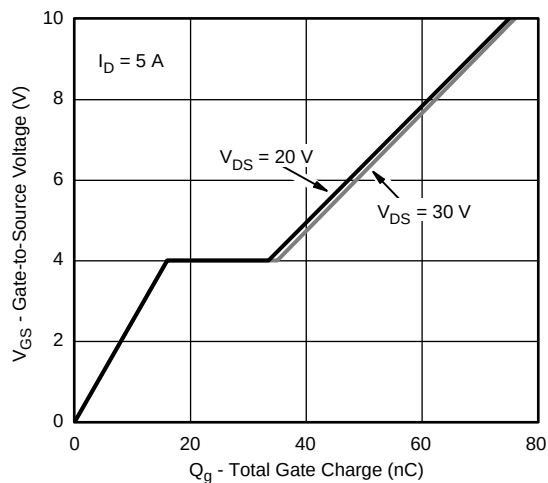
Notes:

a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

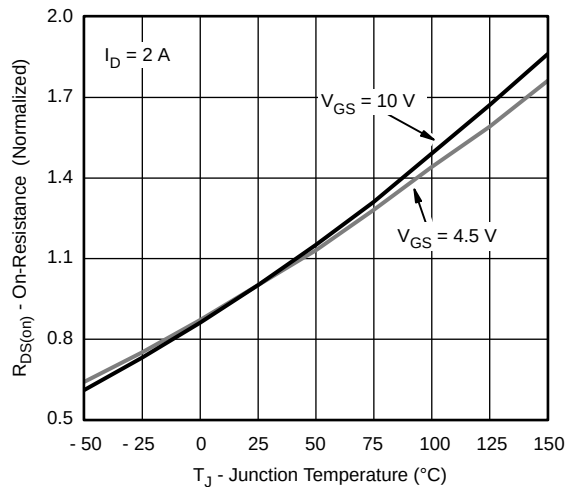
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

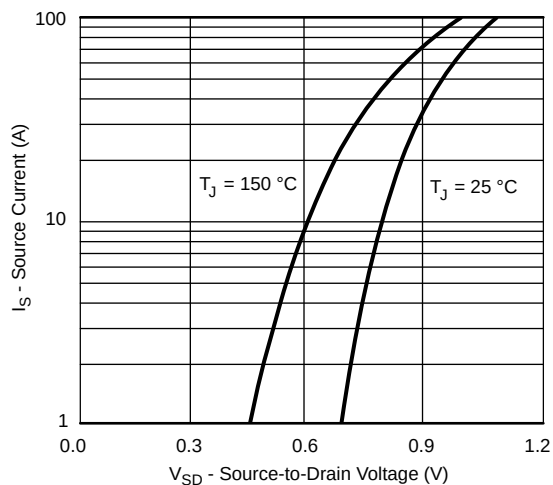
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

Transfer Characteristics

Transfer Characteristics

Transconductance

On-Resistance vs. Drain Current

Capacitance

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


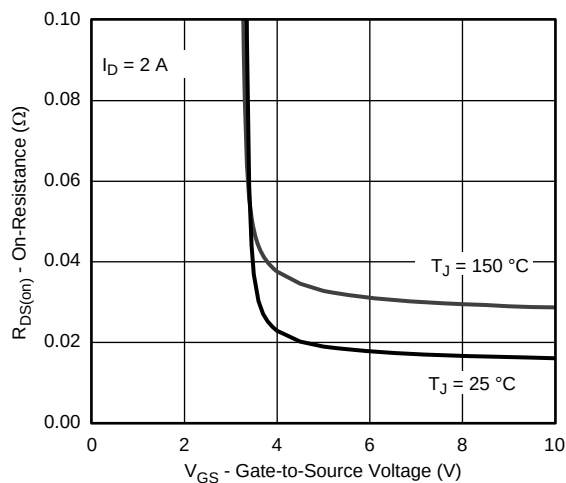
Gate Charge



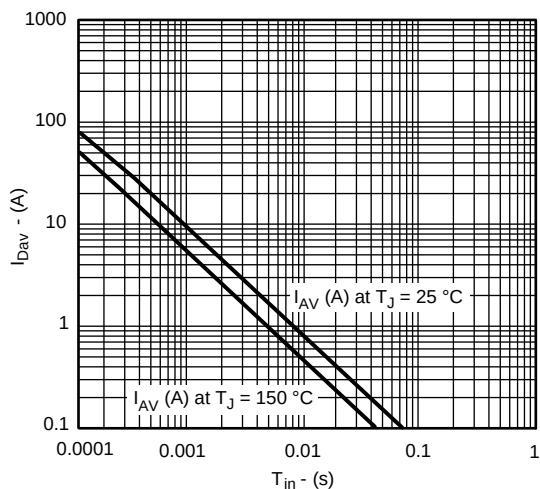
On-Resistance vs. Gate-to-Source Voltage



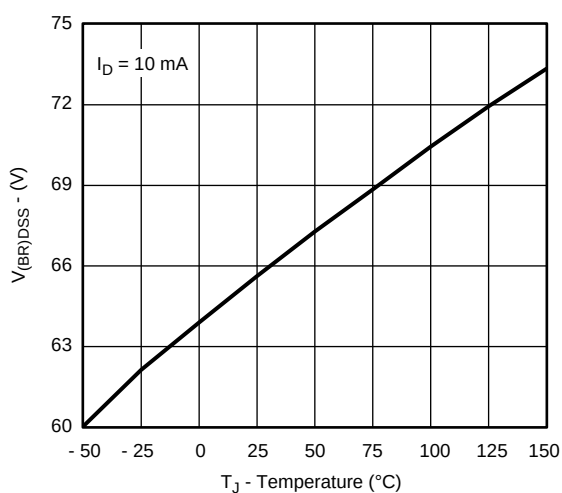
Source-Drain Diode Forward Voltage



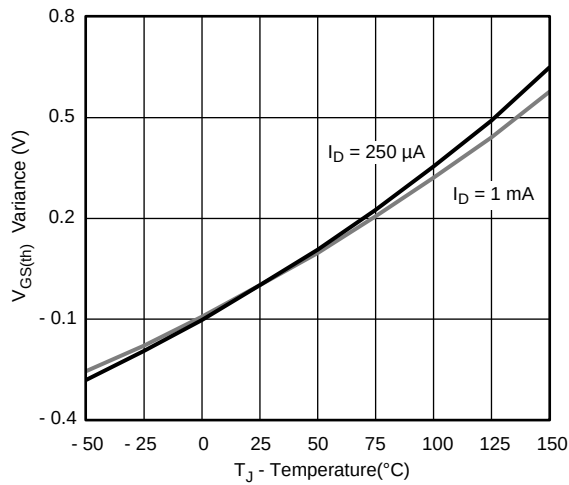
On-Resistance vs. Gate-to-Source Voltage



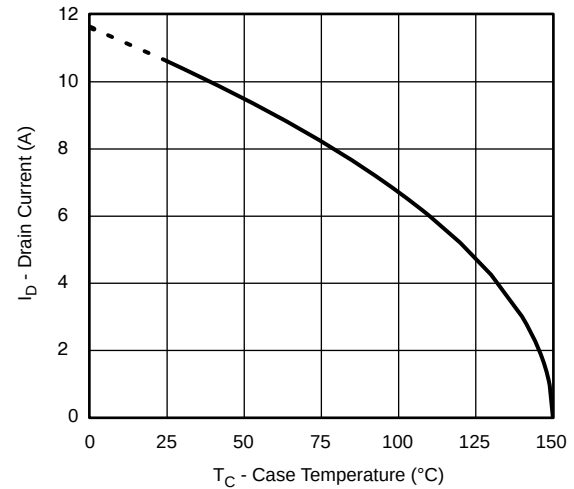
Single Pulse Avalanche Current Capability vs. Time



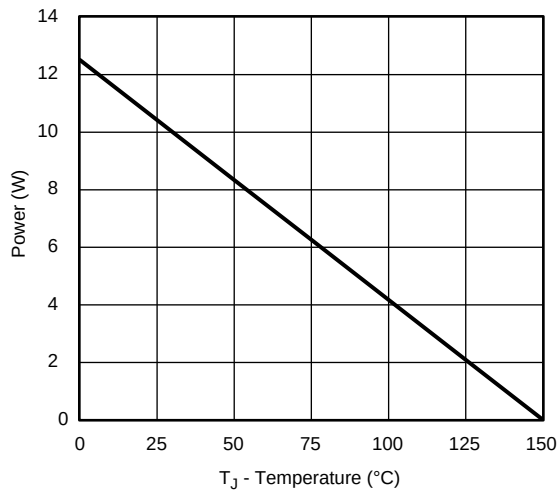
Drain-Source Breakdown Voltage vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


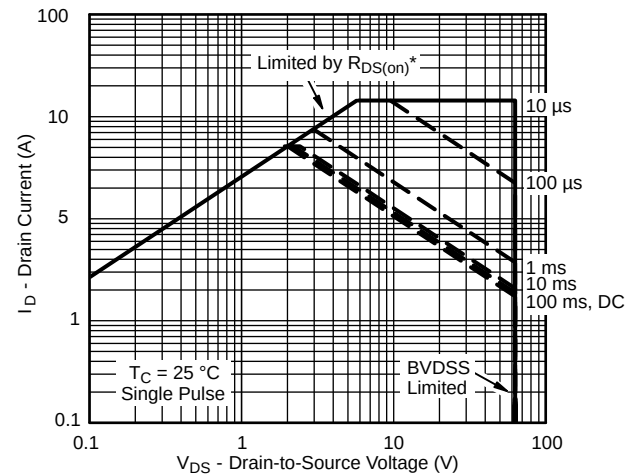
Threshold Voltage



Max. Drain Current vs. Case Temperature

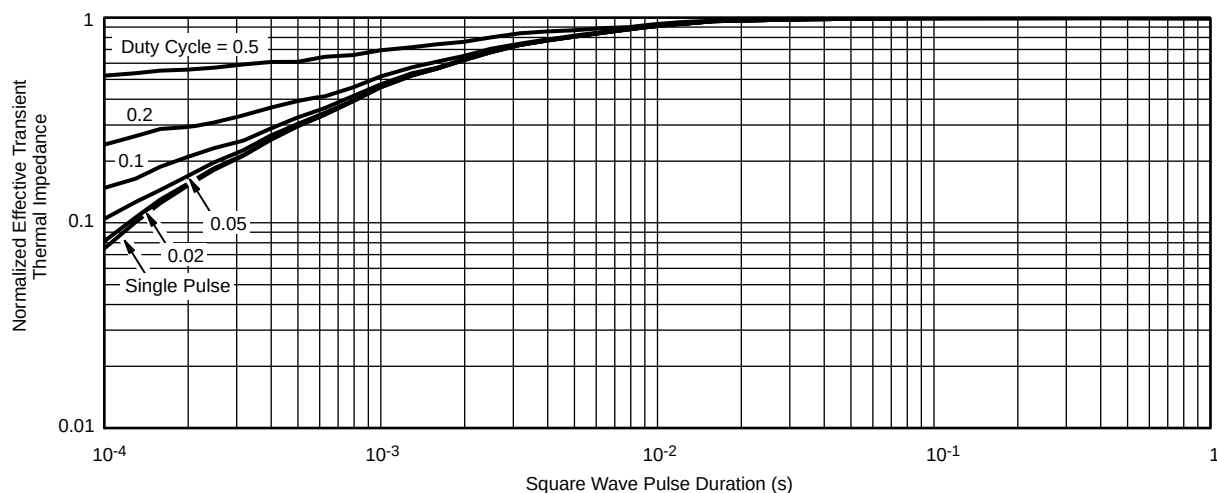


Power Derating, Junction-to-Case



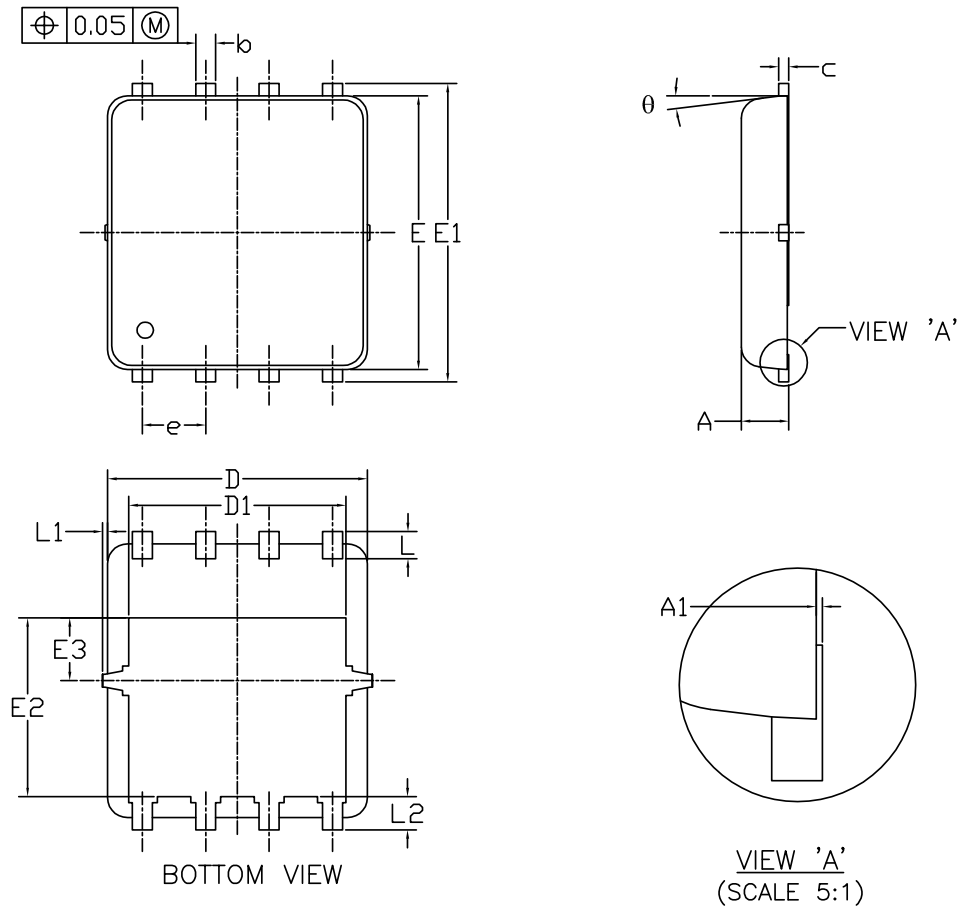
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case

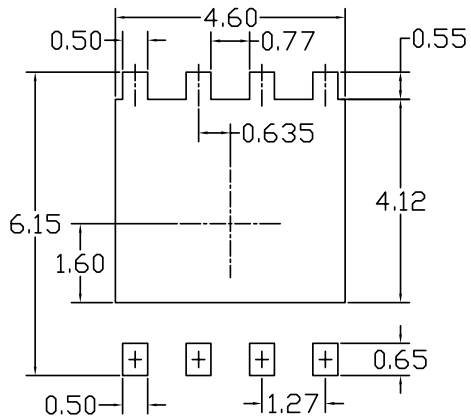


Normalized Thermal Transient Impedance, Junction-to-Case

DFN5x6_8L_EP1_P PACKAGE OUTLIN



RECOMMENDED LAND PATTERN



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.85	0.95	1.00	0.033	0.037	0.039
A1	0.00	---	0.05	0.000	---	0.002
b	0.30	0.40	0.50	0.012	0.016	0.020
c	0.15	0.20	0.25	0.006	0.008	0.010
D	5.10	5.20	5.30	0.201	0.205	0.209
D1	4.25	4.35	4.45	0.167	0.171	0.175
E	5.45	5.55	5.65	0.215	0.219	0.222
E1	5.95	6.05	6.15	0.234	0.238	0.242
E2	3.525	3.625	3.725	0.139	0.143	0.147
E3	1.175	1.275	1.375	0.046	0.050	0.054
e	1.27 BSC			0.050 BSC		
L	0.45	0.55	0.65	0.018	0.022	0.026
L1	0	---	0.15	0	---	0.006
L2	0.68 REF			0.027 REF		
θ	0°	---	10°	0°	---	10°

NOTE

UNIT: mm

- PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
MOLD FLASH AT THE NON-LEAD SIDES SHOULD BE LESS THAN 6 MILS EACH.
- CONTROLLING DIMENSION IS MILLIMETER.
CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

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